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PTO/SB/17 (12-04v2)

Approved for use through 7/31/2006. OMB 0651-0032
U.S. Patent and Trademark Office; U.S. DEPARTMENT OF COMMERCE

Under the Paperwork Reduction Act of 1995, no person are required to respond to a collection of information unless it displays a valid OMB control number.

FEE TRANSMITTAL For FY 2005 <input type="checkbox"/> Applicant claims small entity status. See 37 CFR 1.27		Complete if Known	
		Application Number	Patent#: 6,847,535 B2
		Filing Date	Issued: January 25, 2005
		First Named Inventor	Terry L. Gilton
		Examiner Name	T. Q. Phan
		Art Unit	2818
TOTAL AMOUNT OF PAYMENT		(\$)	100.00
		Attorney Docket No.	M4065.0482/P482

METHOD OF PAYMENT (check all that apply)	
<input type="checkbox"/> Check	<input checked="" type="checkbox"/> Credit Card
<input type="checkbox"/> Money Order	<input type="checkbox"/> None
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<input checked="" type="checkbox"/> Deposit Account	Deposit Account Number: 04-1073 Deposit Account Name: Dickstein Shapiro Morin & Oshinsky LLP
For the above-identified deposit account, the Director is hereby authorized to: (check all that apply)	
<input type="checkbox"/> Charge fee(s) indicated below	<input type="checkbox"/> Charge fee(s) indicated below, except for the filing fee
<input type="checkbox"/> Charge any additional fee(s) or underpayment of fee(s) under 37 CFR 1.16 and 1.17	<input checked="" type="checkbox"/> Credit any overpayments

FEE CALCULATION							
1. BASIC FILING, SEARCH, AND EXAMINATION FEES							
	FILING FEES		SEARCH FEES		EXAMINATION FEES		
		Small Entity		Small Entity		Small Entity	
Application Type	Fee (\$)	Fee (\$)	Fee (\$)	Fee (\$)	Fee (\$)	Fee (\$)	Fees Paid (\$)
Utility	300	150	500	250	200	100	
Design	200	100	100	50	130	65	
Plant	200	100	300	150	160	80	
Reissue	300	150	500	250	600	300	
Provisional	200	100	0	0	0	0	
2. EXCESS CLAIM FEES							
						Fee (\$)	Small Entity Fee (\$)
Fee Description							
Each claim over 20 (including Reissues)						50	25
Each independent claim over 3 (including Reissues)						200	100
Multiple dependent claims						360	180
Total Claims		Extra Claims	Fee (\$)	Fee Paid (\$)	Multiple Dependent Claims		
_____		_____	x _____	= _____	Fee (\$)		Fee Paid (\$)
Indep. Claims		Extra Claims	Fee (\$)	Fee Paid (\$)			
_____		_____	x _____	= _____			
3. APPLICATION SIZE FEE							
If the specification and drawings exceed 100 sheets of paper (excluding electronically filed sequence or computer listings under 37 CFR 1.52(e)), the application size fee due is \$250 (\$125 for small entity) for each additional 50 sheets or fraction thereof. See 35 U.S.C. 41(a)(1)(G) and 37 CFR 1.16(s).							
Total Sheets	Extra Sheets	Number of each additional 50 or fraction thereof		Fee (\$)	Fee Paid (\$)		
_____	_____	/50 _____ (round up to a whole number) x _____		= _____			
4. OTHER FEE(S)							
Non-English Specification, \$130 fee (no small entity discount)						Fees Paid (\$)	
Other (e.g., late filing surcharge): 1811 Certificate of correction						100.00	

SUBMITTED BY			
Signature		Registration No. (Attorney/Agent)	28,371
Name (Print/Type)	Thomas J. D'Amico	Telephone	(202) 828-2232
		Date	December 28, 2005

Certificate
JAN 03 2006
of Correction

JAN 05 2006



Docket No.: M4065.0482/P482
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Letters Patent of:
Terry L. Gilton et al.

Patent No.: 6,847,535 B2

Issued: January 25, 2005

For: REMOVABLE PROGRAMMABLE
CONDUCTOR MEMORY CARD AND
ASSOCIATED READ/WRITE DEVICE AND
METHOD OF OPERATION

REQUEST FOR CERTIFICATE OF CORRECTION
PURSUANT TO 37 C.F.R. §§ 1.322 & 1.323

Attention: Certificate of Correction Branch
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

Upon reviewing the above-identified patent, Patentee noted an omission and several typographical errors which should be corrected.

In the Specification, the USPTO made the following errors:

Column 4, line 49, "card illustrated" **should read** --card 200 inserted within the housing 302 define the location of the memory cells 202 illustrated--; **and**

Column 5, line 44, "which is has" **should read** --which has--;

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JAN 05 2006

In the Specification, Applicants made the following error:

Column 4, line 47, "At shown" should read --As shown--.

In the Claims, the USPTO made the following error:

Claim 27, column 9, line 4, "at cast" should read --at least--.

In the Claims, Applicants made the following error:

Claim 27, column 9, line 6, "at lest" should read --at least--.

In the Other Publications portion of References Cited, the PTO made the following errors:

"Alekperova, Sh.M.; Gadzhleva, G.S., Current-Voltage characteristics of Ag₂Se single crystal near the phase transition, Inorganic Materials 23 (1987) 137-139."

Should read:

--Alekperova, Sh.M.; Gadzhleva, G.S., Current-Voltage characteristics of Ag₂Se single crystal near the phase transition, Inorganic Materials 23 (1987) 137-139.--;

"Elliot, S.R., Photodissolution of metals in chalcogenide glasses: A unified mechanism, J. Non-Cryst. Solids 137-138 (1991) 1031-1034."

Should read:

--Elliott, S.R., Photodissolution of metals in chalcogenide glasses: A unified mechanism, J. Non-Cryst. Solids 137-138 (1991) 1031-1034.--;

"Tranchant, S.; Peytavin, S.; Ribes, M.; Flank, A.M.; Dexpert, H.; Lagarde, J.P., Silver chalcogenide glasses Ag-Ge-Se: Ionic conduction and exafs structural investigation, Transport-structure relation in fast ion and mixed conductors Proceedings of the 6th Riso International symposium, Sep. 9-13, 1985."

Should read:

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“Welrauch, D.F., Threshold switching and thermal filaments in amorphous semiconductors, App. Phys. Lett. 16 (1970) 72-73.”

Should read:

--Weirauch, D.F., Threshold switching and thermal filaments in amorphous semiconductors, App. Phys. Lett. 16 (1970) 72-73.--.

The errors were both found in the application as filed by applicants and made by the USPTO. Please charge our Credit Card in the amount of \$100.00 covering the fee set forth in 37 CFR 1.20(a). Credit Card Payment Form SB-2038, with a signature from an authorized cardholder, is enclosed. The errors now sought to be corrected are inadvertent typographical errors the correction of which does not involve new matter or require reexamination. Transmitted herewith is a proposed Certificate of Correction effecting such amendment. Patentee respectfully solicits the granting of the requested Certificate of Correction.

The Director is hereby authorized to charge any deficiency in the fees filed, asserted to be filed or which should have been filed herewith (or with any paper hereafter filed in this application by this firm) to our Deposit Account No. 04-1073, under Order No. M4065.0482/P482.

Dated: December 28, 2005

Respectfully submitted,

By 

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**UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION**

Page 1 of 2

PATENT NO. : 6,847,535 *B2*
APPLICATION NO. : 10/077,784
ISSUE DATE : January 25, 2005
INVENTOR(S) : Terry L. Gilton et al.

It is certified that errors appear in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

In the Specification, the following errors are corrected:

Column 4, line 47, "At shown" should read --As shown--;

Column 4, line 49, "card illustrated" should read --card 200 inserted within the housing 302 define the location of the memory cells 202 illustrated--; and

Column 5, line 45, "which is has" should read --which has--.

In the Claims, the following errors are corrected:

Claim 27, Column 9, line 4, "at cast" should read --at least--; and

Claim 27, column 9, line 6, "at lest" should read --at least--.

In the Other Publications portion of References Cited, the following errors are corrected:

"Alekperova, Sh.M.; Gadzhleva, G.S., Current-Voltage characteristics of Ag₂Se single crystal near the phase transition, Inorganic Materials 23 (1987) 137-139."

Should read:

--Alekperova, Sh.M.; Gadzhleva, G.S., Current-Voltage characteristics of Ag₂Se single crystal near the phase transition, Inorganic Materials 23 (1987) 137-139.--;

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DSMDB.1997366.1

JAN 05 2006

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Should read:

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